

Amendments to the Claims:

This listing of claims will replace all prior versions and listing of claims in the application:

Listing of Claims:

- 5 1. (Currently amended) A pixel structure of an active matrix display device, the active matrix display device having a source of first potential and a source of second potential, the pixel structure comprising:
- a plurality of active-type light emitting devices connected in parallel with each other, each of the active-type light emitting devices being electrically connected between
- 10 the source of first potential and the source of second potential;
- a first active device having a first end electrically connected to a scanning line, a second end electrically connected to a data line, and a third end electrically connected to a switching end of each of the active-type light emitting devices for switching all of the active-type light emitting devices simultaneously; wherein the
- 15 ~~active-type light emitting devices being electrically connected to the first active device as many to one mapping relation; and~~
- a storage capacitor having a first electrode electrically connected to the third end of the first active device and the switching end of the active-type light emitting devices, and a second electrode electrically connected to the source of first potential
- 20 end.
2. (Original) The pixel structure of claim 1, wherein the first active device is a first thin film transistor, and the first end is a gate electrode of the first thin film transistor, the second end is a drain electrode of the first thin film transistor, and the third end is a

source electrode of the first thin film transistor.

3. (Previously presented) The pixel structure of claim 1, wherein the storage capacitor is electrically connected between the third end of the first active device and
5 the source of first potential.

4. (Previously presented) The pixel structure of claim 3, wherein the source of first potential is utilized for supplying a constant potential.

10 5. (Previously presented) The pixel structure of claim 1, wherein each of the active-type light emitting devices comprises:

a second active device having a fourth end electrically connected to the third end of the first active device, a fifth end connected to the source of first potential, and a sixth end, wherein the fourth end is the switching end; and

15 a light emitting device having a seventh end connected to the sixth end and an eighth end connected to the source of second potential.

6. (Previously presented) The pixel structure of claim 5, wherein when an electrical shortage occurs in one of the active-type light emitting devices, the pixel structure
20 displays an image via the other active-type light emitting devices.

7. (Original) The pixel structure of claim 5, wherein each of the second active devices comprises a second thin film transistor or a complementary metal-oxide semiconductor (CMOS).

8. (Original) The pixel structure of claim 7, wherein the fourth end is a gate electrode of the second thin film transistor, the fifth end is a source electrode of the second thin film transistor, and the sixth end is a drain electrode of the second thin film transistor.

9. (Original) The pixel structure of claim 5, wherein each of the light emitting devices comprises an organic light emitting diode (OLED) or a light emitting diode (LED).

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10. (Original) The pixel structure of claim 9, wherein the seventh end is an anode of the light emitting device, and the eighth end serves as a cathode of the light emitting device.

11. (Currently amended) An active matrix display device comprising:
a plurality of scanning lines;
a plurality of data lines;
a plurality of pixels, each of the pixels electrically connected to one corresponding scanning line and one corresponding data line, each of the pixels comprising:

a first active device having a first end electrically connected to the corresponding scanning line, a second end electrically connected to the corresponding data line, and a third end;

a plurality of active-type light emitting devices electrically connected in parallel with each other, each of the active-type light emitting devices being connected

between a source of first potential and a source of second potential, ~~wherein the active-type light emitting devices being electrically connected to the first active device as many to one mapping relation;~~ each of the active-type light emitting devices comprising:

5 a light emitting device electrically connected to the source of second potential; and

 a second active device having a fourth end electrically connected to the third end, a fifth end electrically connected to the source of first potential, and a sixth end electrically connected to the light emitting device, wherein the first active device switches all of the active-type light emitting devices simultaneously; and

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 a storage capacitor having a first electrode electrically connected to the third end of the first active device and the fourth end of the active-type light emitting devices, and a second electrode electrically connected to the source of first potential end.

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12. (Original) The active matrix display device of claim 11, wherein the first active device is a first thin film transistor, and the first end is a gate electrode of the first thin film transistor, the second end is a drain electrode of the first thin film transistor, and

20 the third end is a source electrode of the first thin film transistor.

13. (Previously presented) The active matrix display device of claim 11, wherein the storage capacitor is electrically connected between the third end of the active device and the source of first potential that is utilized for supplying a constant potential.

14. (Previously presented) The active matrix display device of claim 13, wherein the source of first potential is utilized for supplying a constant potential.

5 15. (Original) The active matrix display device of claim 11, wherein each of the second active devices comprises a second thin film transistor or a complementary metal-oxide semiconductor (CMOS).

16. (Original) The active matrix display device of claim 15, wherein the fourth end is
10 a gate electrode of the second thin film transistor, the fifth end is a source electrode of the second thin film transistor, and the sixth end is a drain electrode of the second thin film transistor.

17. (Original) The active matrix display device of claim 11, wherein each of the light
15 emitting devices comprises an organic light emitting diode (OLED) or a light emitting diode (LED).

18. (Previously presented) The active matrix display device of claim 11, wherein
when an electrical shortage occurs in one of the active-type light emitting devices of a
20 pixel, the pixel displays an image via the other active-type light emitting devices of the pixel.